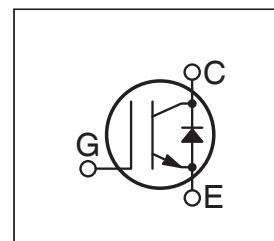
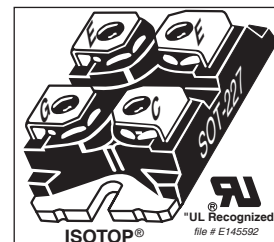


POWER MOS 7® IGBT

The POWER MOS 7® IGBT is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

- Low Conduction Loss
- SSOA Rated
- Low Gate Charge
- Ultrafast Tail Current shutoff



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT40GP90JDQ2	UNIT
V_{CES}	Collector-Emitter Voltage	900	Volts
V_{GE}	Gate-Emitter Voltage	± 30	
I_{C1}	Continuous Collector Current ^⑦ @ $T_C = 25^\circ\text{C}$	64	Amps
I_{C2}	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	27	
I_{CM}	Pulsed Collector Current ^①	160	
SSOA	Switching Safe Operating Area @ $T_J = 150^\circ\text{C}$	160A @ 900V	
P_D	Total Power Dissipation	284	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 350\mu A$)	900			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 1mA, T_J = 25^\circ\text{C}$)	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 40A, T_J = 25^\circ\text{C}$)		3.2	3.9	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = 40A, T_J = 125^\circ\text{C}$)		2.7		
I_{CES}	Collector Cut-off Current ($V_{CE} = 900V, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			350	μA
	Collector Cut-off Current ($V_{CE} = 900V, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			1500	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V$)			± 100	nA



CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

DYNAMIC CHARACTERISTICS

APT40GP90JDQ2

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{ies}	Input Capacitance	Capacitance $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		3300		pF
C_{oes}	Output Capacitance			325		
C_{res}	Reverse Transfer Capacitance			35		
V_{GEP}	Gate-to-Emitter Plateau Voltage	Gate Charge $V_{GE} = 15V$ $V_{CE} = 450V$ $I_C = 40A$		7.5		V
Q_g	Total Gate Charge ^③			145		nC
Q_{ge}	Gate-Emitter Charge			22		
Q_{gc}	Gate-Collector ("Miller") Charge			55		
SSOA	Switching Safe Operating Area	$T_J = 150^\circ C, R_G = 4.3\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 900V$	160			A
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 4.3\Omega$ $T_J = +25^\circ C$		14		ns
t_r	Current Rise Time			23		
$t_{d(off)}$	Turn-off Delay Time			90		
t_f	Current Fall Time			60		
E_{on1}	Turn-on Switching Energy ^④			TBD		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			1350		
E_{off}	Turn-off Switching Energy ^⑥			795		
$t_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 40A$ $R_G = 4.3\Omega$ $T_J = +125^\circ C$		14		ns
t_r	Current Rise Time			23		
$t_{d(off)}$	Turn-off Delay Time			130		
t_f	Current Fall Time			90		
E_{on1}	Turn-on Switching Energy ^④			TBD		μJ
E_{on2}	Turn-on Switching Energy (Diode) ^⑤			2280		
E_{off}	Turn-off Switching Energy ^⑥			1245		

THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.44	$^\circ C/W$
$R_{\theta JC}$	Junction to Case (DIODE)			1.1	
W_T	Package Weight		29.2		gm
$V_{Isolation}$	RMS Voltage (50-60Hz Sinusoidal Waveform From Terminals to Mounting Base for 1 Min.)	2500			Volts

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices, I_{ces} includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④ E_{on1} is the clamped inductive turn-on energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. Tested in inductive switching test circuit shown in figure 21, but with a Silicon Carbide diode.

⑤ E_{on2} is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥ E_{off} is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

⑦ Continuous current limited by package lead temperature.

APT Reserves the right to change, without notice, the specifications and information contained h

TYPICAL PERFORMANCE CURVES

APT40GP90JDQ2

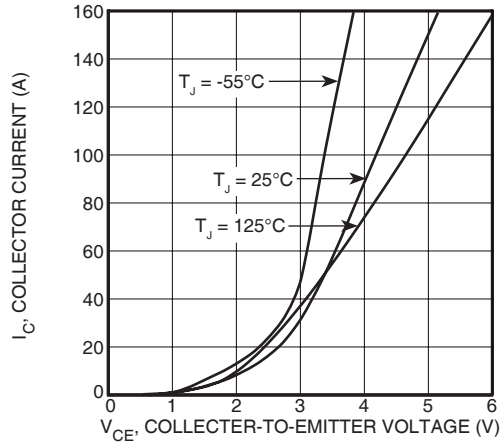


FIGURE 1, Output Characteristics($T_J = 25^{\circ}\text{C}$)

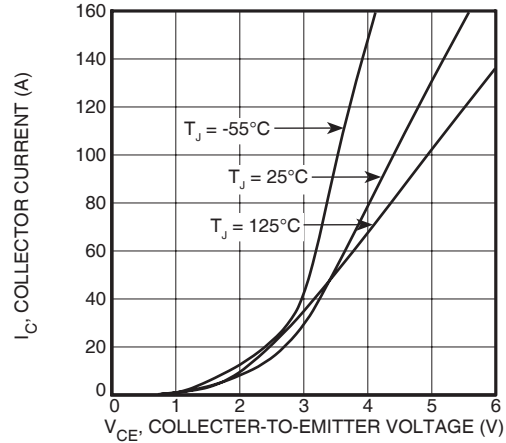


FIGURE 2, Output Characteristics ($T_J = 125^{\circ}\text{C}$)

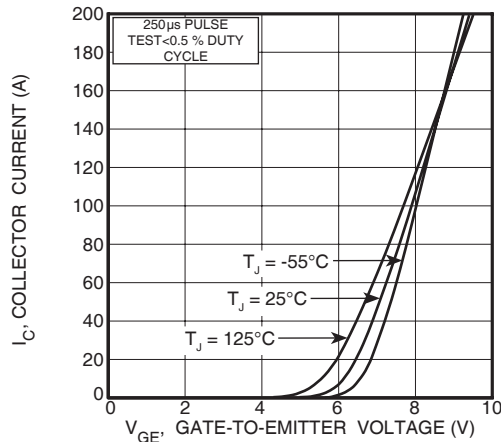


FIGURE 3, Transfer Characteristics

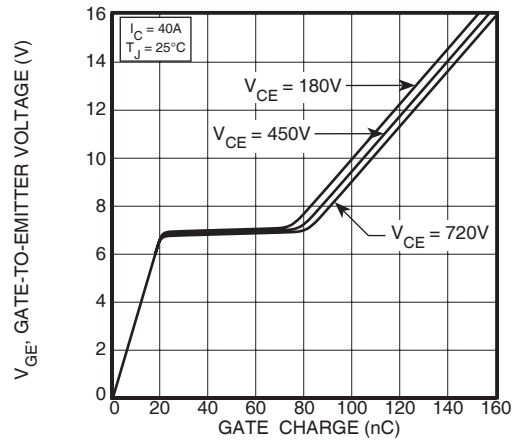


FIGURE 4, Gate Charge

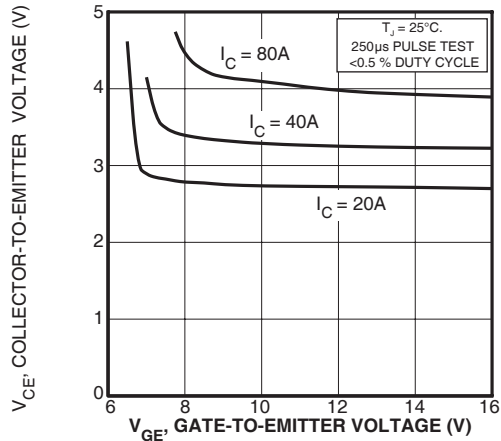


FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage

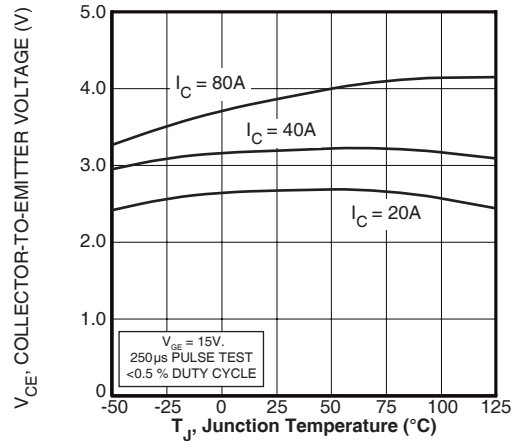


FIGURE 6, On State Voltage vs Junction Temperature

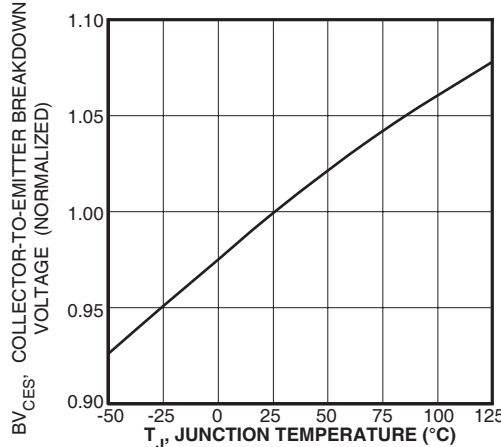


FIGURE 7, Breakdown Voltage vs. Junction Temperature

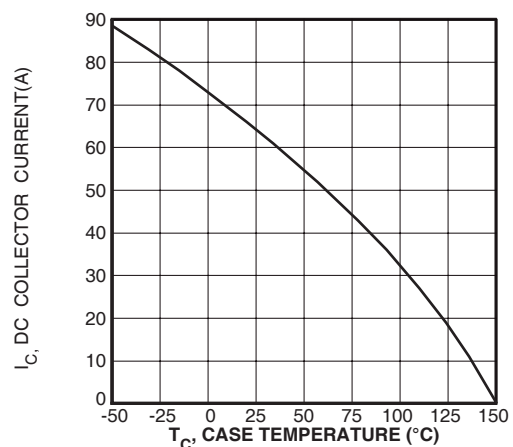


FIGURE 8, DC Collector Current vs Case Temperature

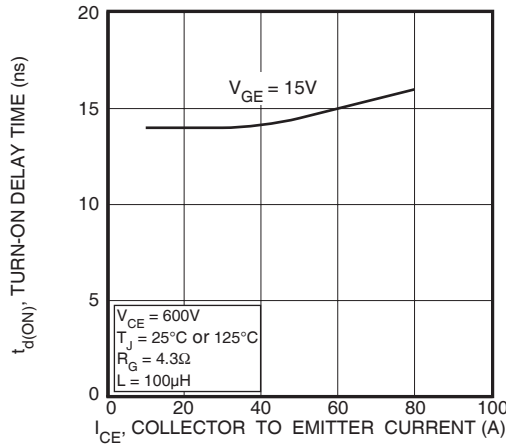


FIGURE 9, Turn-On Delay Time vs Collector Current

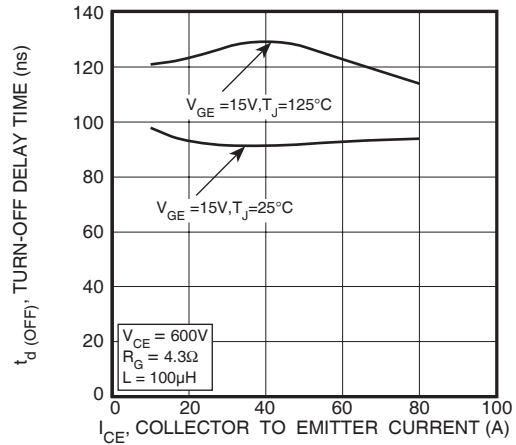


FIGURE 10, Turn-Off Delay Time vs Collector Current

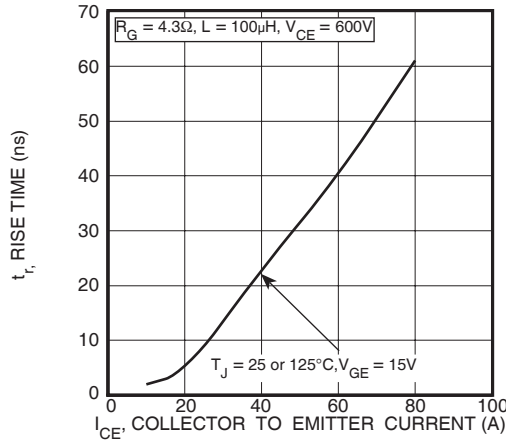


FIGURE 11, Current Rise Time vs Collector Current

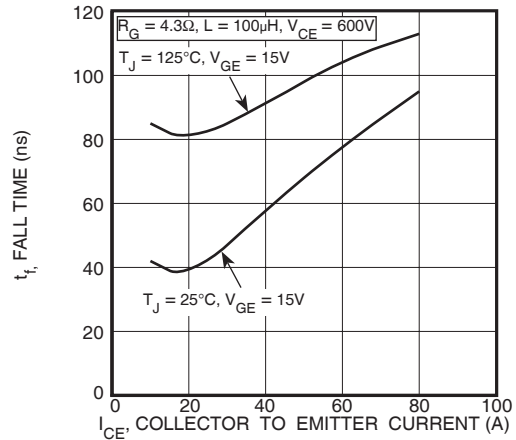


FIGURE 12, Current Fall Time vs Collector Current

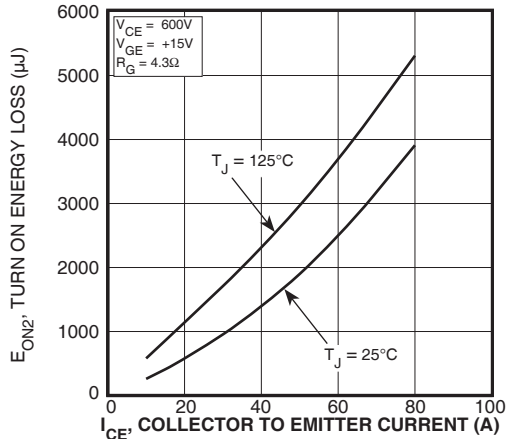


FIGURE 13, Turn-On Energy Loss vs Collector Current

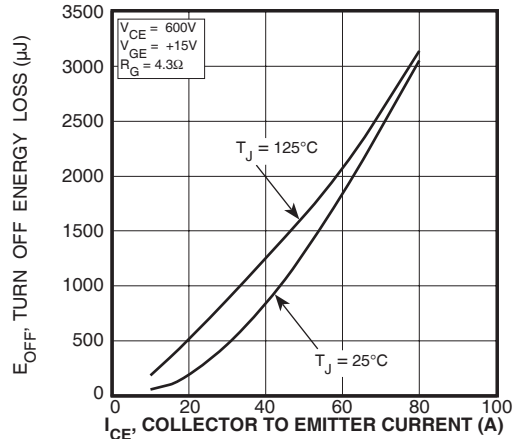


FIGURE 14, Turn Off Energy Loss vs Collector Current

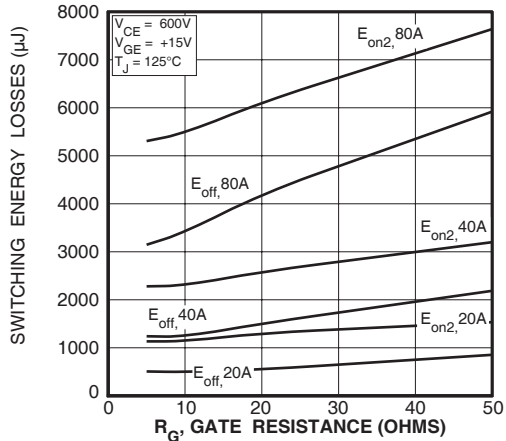


FIGURE 15, Switching Energy Losses vs. Gate Resistance

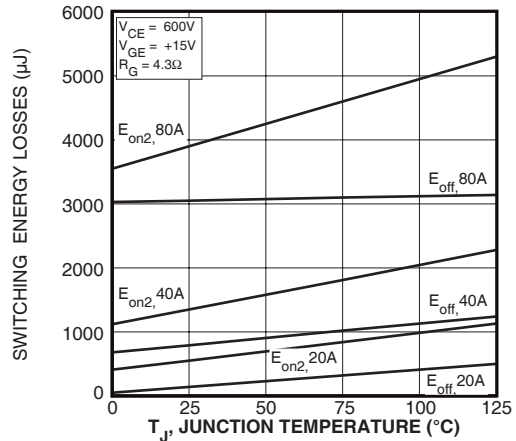


FIGURE 16, Switching Energy Losses vs Junction Temperature

TYPICAL PERFORMANCE CURVES

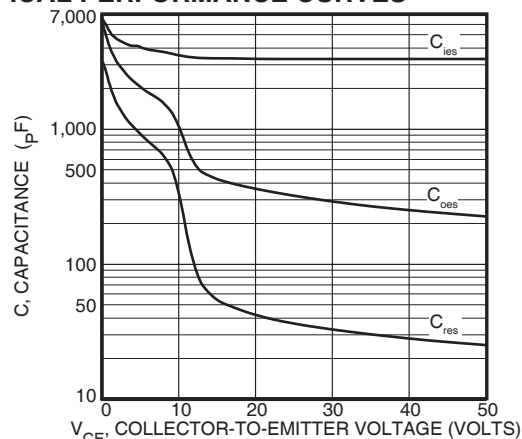


Figure 17, Capacitance vs Collector-To-Emitter Voltage

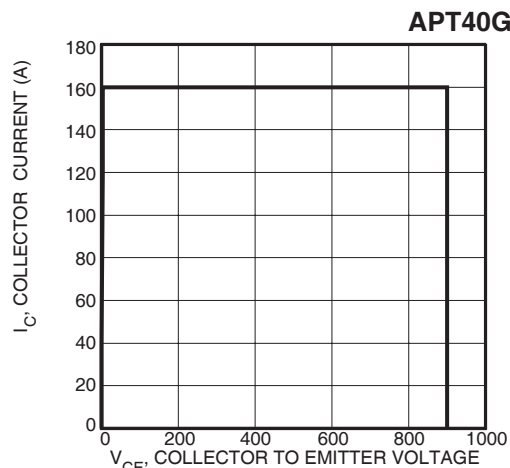


Figure 18, Minimum Switching Safe Operating Area

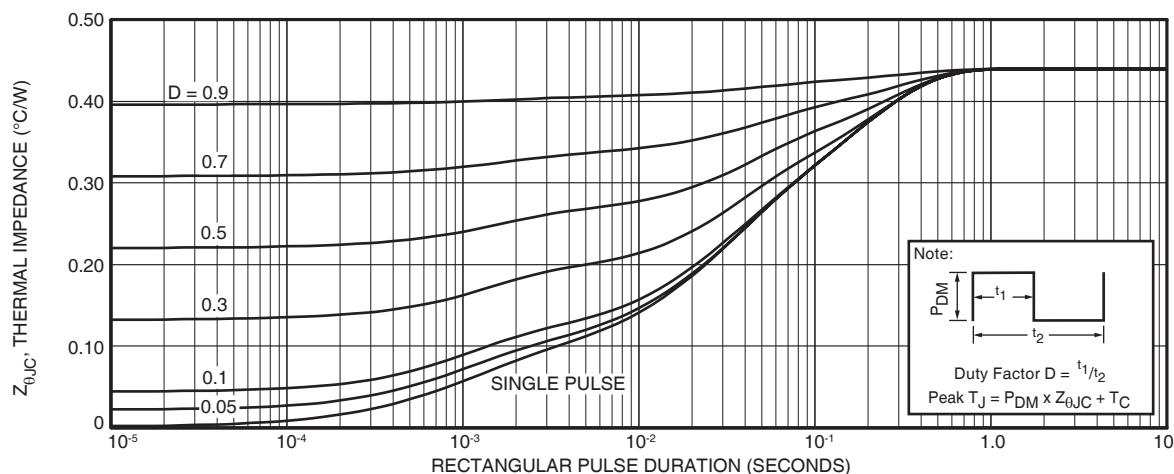


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

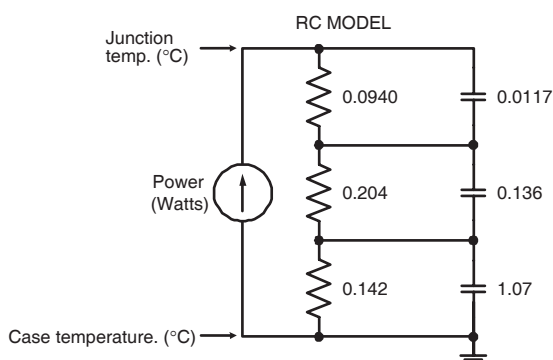


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

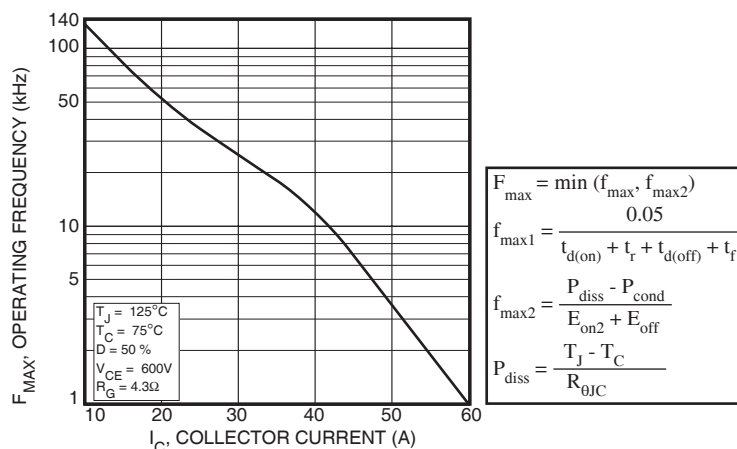


Figure 20, Operating Frequency vs Collector Current

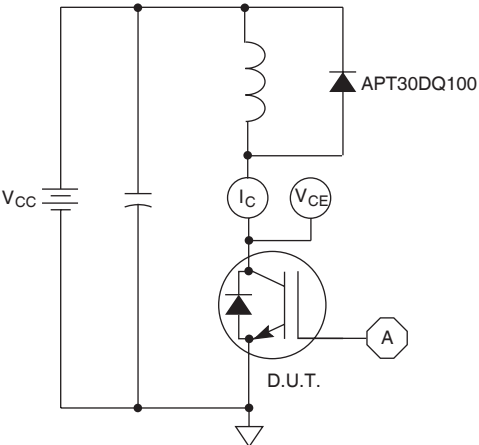


Figure 21, Inductive Switching Test Circuit

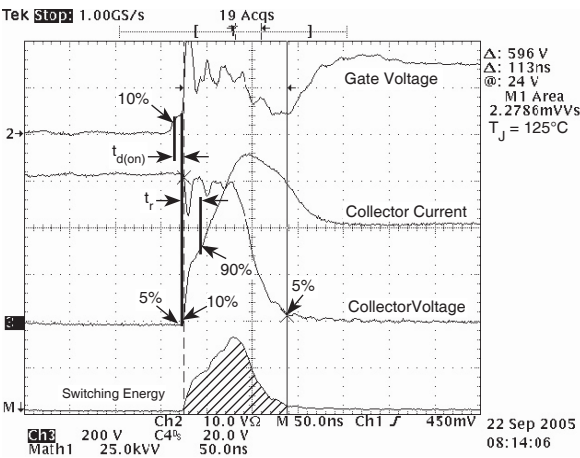


Figure 22, Turn-on Switching Waveforms and Definitions

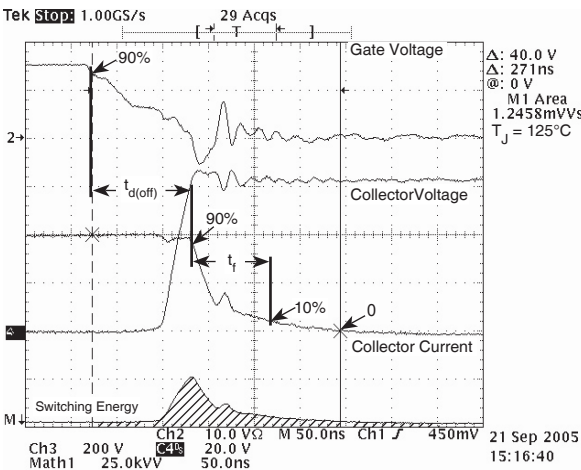


Figure 23, Turn-off Switching Waveforms and Definitions

ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT40GP90JDQ2			UNIT
$I_F(\text{AV})$	Maximum Average Forward Current ($T_C = 92^\circ\text{C}$, Duty Cycle = 0.5)		30		Amps
$I_F(\text{RMS})$	RMS Forward Current (Square wave, 50% duty)		39		
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)		210		

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
V_F	Forward Voltage	$I_F = 30\text{A}$		2.3		Volts
		$I_F = 60\text{A}$		2.8		
		$I_F = 30\text{A}$, $T_J = 125^\circ\text{C}$		1.7		

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
t_{rr}	Reverse Recovery Time	$I_F = 1\text{A}$, $di_F/dt = -100\text{A}/\mu\text{s}$, $V_R = 30\text{V}$, $T_J = 25^\circ\text{C}$	-	25		ns
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$, $di_F/dt = -200\text{A}/\mu\text{s}$ $V_R = 667\text{V}$, $T_C = 25^\circ\text{C}$	-	240		
Q_{rr}	Reverse Recovery Charge		-	355		nC
I_{RRM}	Maximum Reverse Recovery Current		-	4	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$, $di_F/dt = -200\text{A}/\mu\text{s}$ $V_R = 667\text{V}$, $T_C = 125^\circ\text{C}$	-	305		ns
Q_{rr}	Reverse Recovery Charge		-	1575		nC
I_{RRM}	Maximum Reverse Recovery Current		-	9	-	Amps
t_{rr}	Reverse Recovery Time	$I_F = 30\text{A}$, $di_F/dt = -1000\text{A}/\mu\text{s}$ $V_R = 667\text{V}$, $T_C = 125^\circ\text{C}$	-	135		ns
Q_{rr}	Reverse Recovery Charge		-	2270		nC
I_{RRM}	Maximum Reverse Recovery Current		-	27		Amps

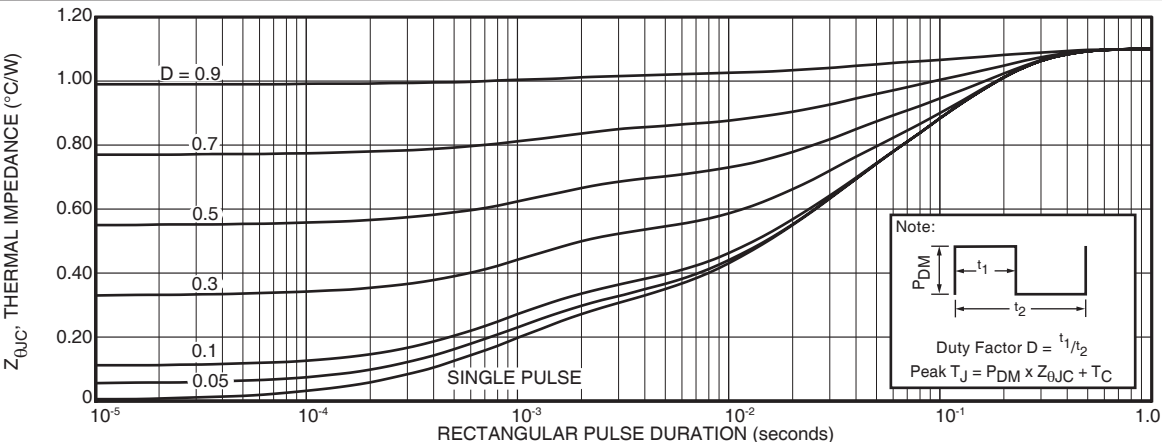


FIGURE 24a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

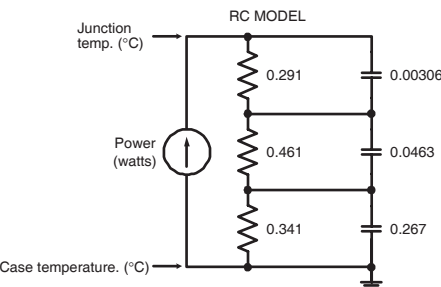


FIGURE 24b. TRANSIENT THERMAL IMPEDANCE MODEL

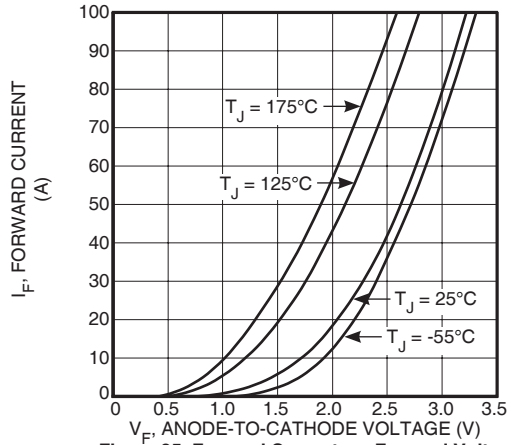


Figure 25. Forward Current vs. Forward Voltage

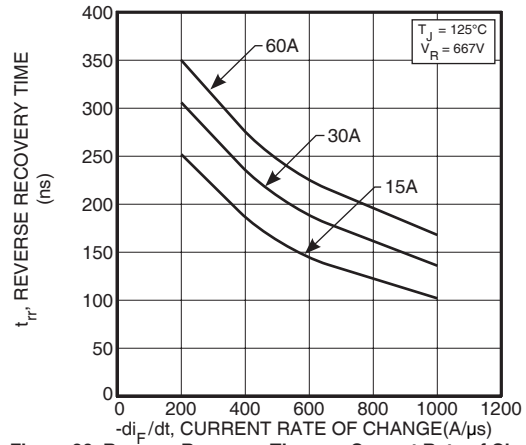


Figure 26. Reverse Recovery Time vs. Current Rate of Change

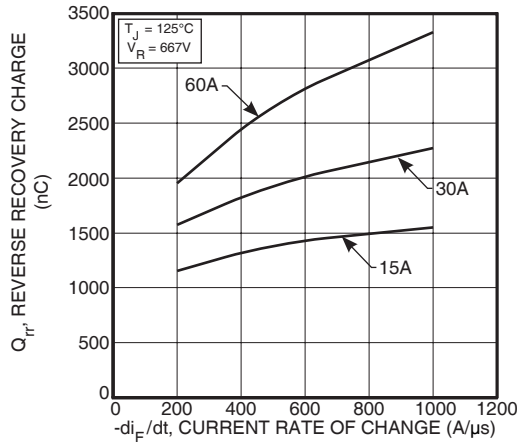


Figure 27. Reverse Recovery Charge vs. Current Rate of Change

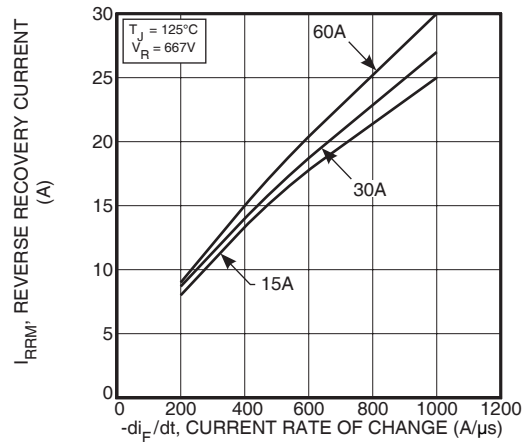


Figure 28. Reverse Recovery Current vs. Current Rate of Change

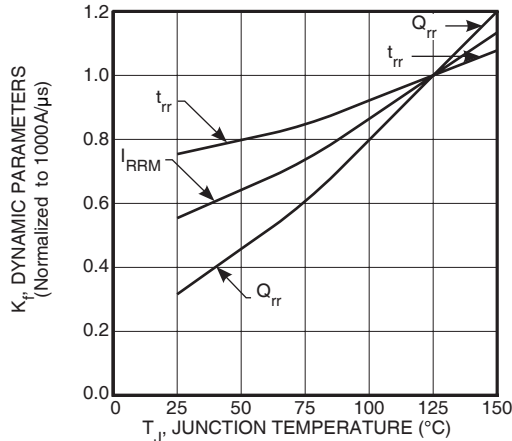


Figure 29. Dynamic Parameters vs. Junction Temperature

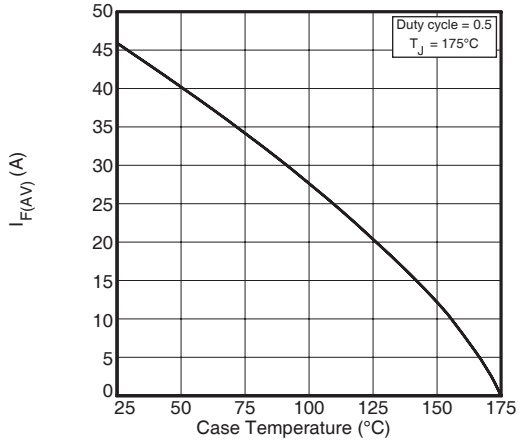


Figure 30. Maximum Average Forward Current vs. Case Temperature

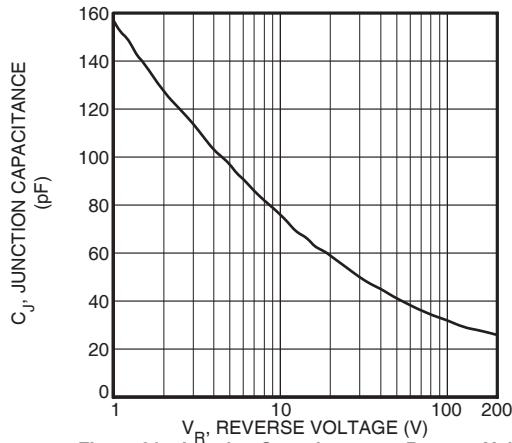


Figure 31. Junction Capacitance vs. Reverse Voltage

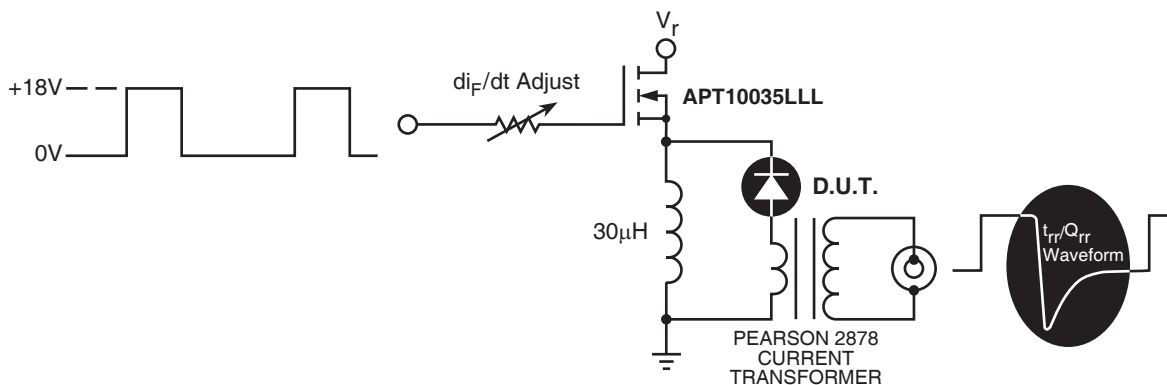


Figure 32. Diode Test Circuit

- ➊ I_F - Forward Conduction Current
- ➋ di_F/dt - Rate of Diode Current Change Through Zero Crossing.
- ➌ I_{RRM} - Maximum Reverse Recovery Current.
- ➍ t_{rr} - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through I_{RRM} and $0.25 \cdot I_{RRM}$ passes through zero.
- ➎ Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

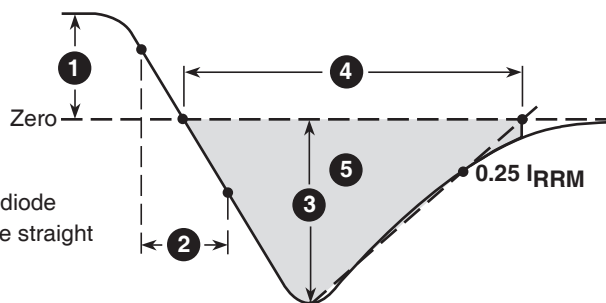
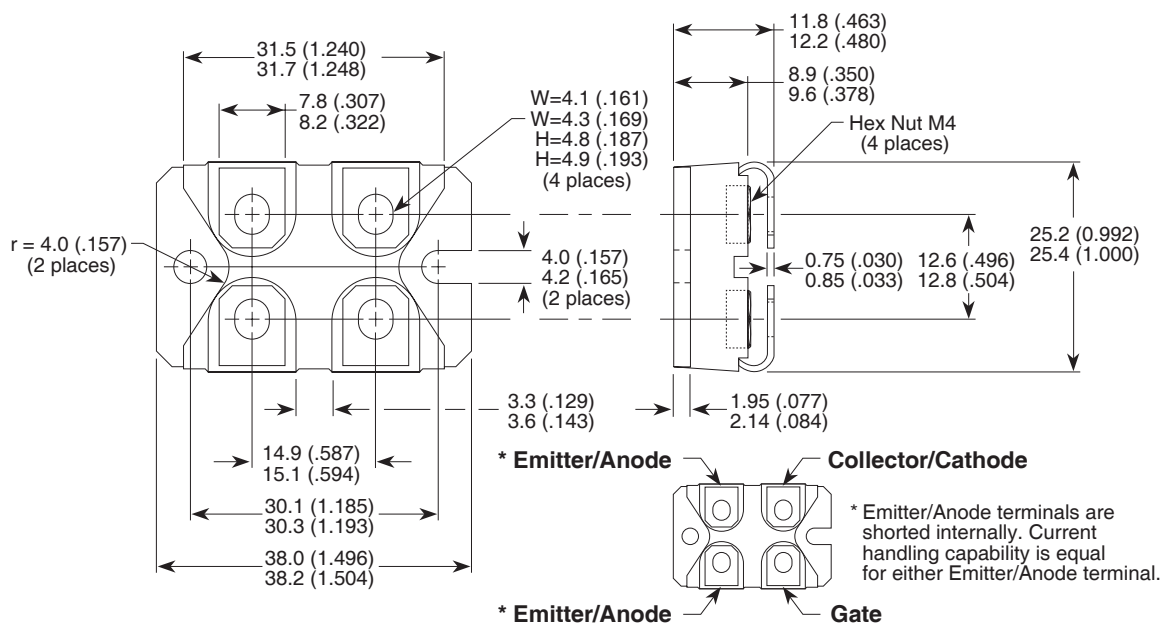


Figure 33, Diode Reverse Recovery Waveform and Definitions

SOT-227 (ISOTOP®) Package Outline



Dimensions in Millimeters and (Inches)

ISOTOP® is a Registered Trademark of SGS Thomson. APT's products are covered by one or more of U.S. patents 4,895,810 5045,903 5089,434 5182,234 5019,522 5,262,336 6503,786 5256,583 4748,103 5283,202 5231,474 5434,095 5528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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Электронная почта: org@eplast1.ru

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